

NPN Silicon General Purpose Amplifier Transistor

This NPN transistor is designed for general purpose amplifier applications. This device is housed in the SC-75/SOT-416 package which is designed for low power surface mount applications, where board space is at a premium.

Features

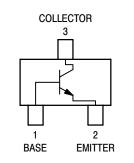
- Pb–Free Package is Available*
- Reduces Board Space
- High h_{FE}, 210–460 (typical)
- Low V_{CE(sat)}, < 0.5 V
- Available in 8 mm, 7 inch/3000 Unit Tape and Reel



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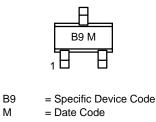
NPN GENERAL PURPOSE AMPLIFIER TRANSISTORS SURFACE MOUNT





SC-75 CASE 463 STYLE 1

MARKING DIAGRAM



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MAXIMUM BATINGS HTRT # CO

Rating	Symbol	Value	Unit
Collector-Base Voltage	V _{(BR)CBO}	50	Vdc
Collector-Emitter Voltage	V _{(BR)CEO}	50	Vdc
Emitter-Base Voltage	V _{(BR)EBO}	5.0	Vdc
Collector Current – Continuous	Ι _C	100	mAdc

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 1)	PD	125	mW
Junction Temperature	TJ	150	°C
Storage Temperature Range	T _{stg}	-55 ~ +150	°C

1. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$)

Characteristic	Symbol	Min	Тур	Max	Unit
Collector-Base Breakdown Voltage (I _C = 50 μ Adc, I _E = 0)	V _{(BR)CBO}	50	-	-	Vdc
Collector-Emitter Breakdown Voltage ($I_C = 1.0 \text{ mAdc}, I_B = 0$)	V _{(BR)CEO}	50	-	-	Vdc
Emitter-Base Breakdown Voltage ($I_E = 50 \ \mu Adc$, $I_E = 0$)	V _{(BR)EBO}	5.0	-	-	Vdc
Collector-Base Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)	I _{CBO}	-	-	0.5	μΑ
Emitter-Base Cutoff Current ($V_{EB} = 4.0 \text{ Vdc}$, $I_B = 0$)	I _{EBO}	-	-	0.5	μΑ
Collector-Emitter Saturation Voltage (Note 2) $(I_{C} = 60 \text{ mAdc}, I_{B} = 5.0 \text{ mAdc})$	V _{CE(sat)}	-	-	0.4	Vdc
DC Current Gain (Note 2) (V_{CE} = 6.0 Vdc, I _C = 1.0 mAdc)	h _{FE}	120	-	560	-
Transition Frequency (V _{CE} = 12 Vdc, I_C = 2.0 mAdc, f = 30 MHz)	f _T	-	180	-	MHz
Output Capacitance (V _{CB} = 12 Vdc, I _C = 0 Adc, f = 1 MHz)	C _{OB}	-	2.0	-	pF

2. Pulse Test: Pulse Width \leq 300 $\mu s,\, D.C. \leq$ 2%.

ORDERING INFORMATION

Device	Package	Shipping [†]
2SC4617	SC-75	3,000 / Tape & Reel
2SC4617G	SC-75 (Pb-Free)	3,000 / Tape & Reel
2SC4617T1	SC-75	3,000 / Tape & Reel
2SC4617T1G	SC-75 (Pb-Free)	3,000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

2SC4617

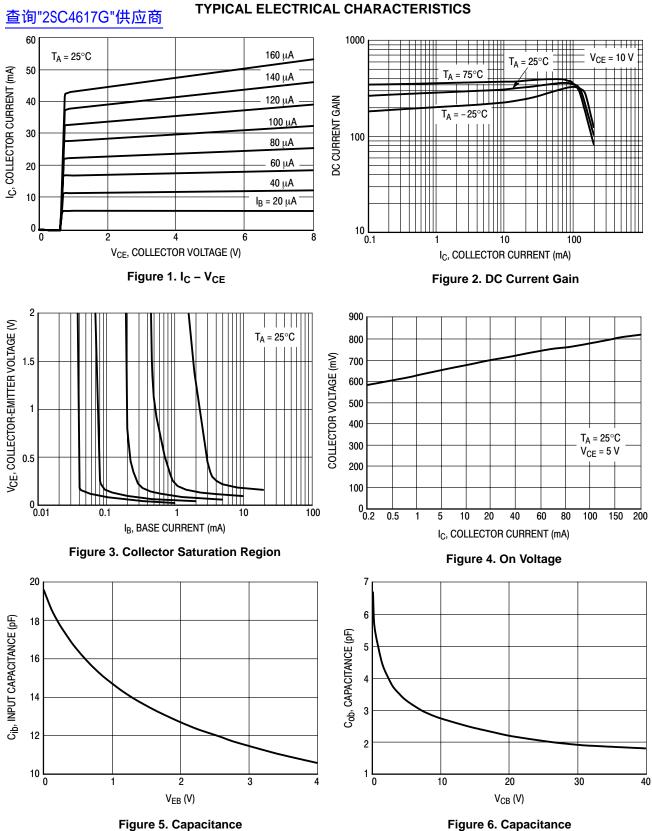
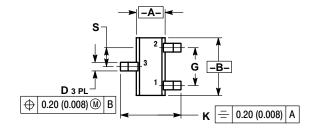


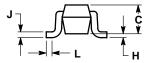
Figure 6. Capacitance

查询"2SC4617G"供应商

PACKAGE DIMENSIONS

SC-75 (SOT-416) CASE 463-01 ISSUE C





NOTES:
1. DIMENSIONING AND TOLERANCING PER
ANSI Y14.5M, 1982.

2. CONTROLLING DIMENSION: MILLIMETE						
		MILLIMETERS		INCHES		
	DIM	MIN MAX		MIN	MAX	
	Α	0.70	0.90	0.028	0.035	
	В	1.40	1.80	0.055	0.071	
	С	0.60	0.90	0.024	0.035	
	D	0.15	0.30	0.006	0.012	
	G	1.00 BSC 0.10		0.039 BSC		
	Н				0.004	
	J	0.10	0.25	0.004	0.010	
	κ	1.45	1.75	0.057	0.069	
	Ĺ	0.10	0.20	0.004	0.008	
	S	0.50	BSC	0.020	0.020 BSC	

STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR

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